MBR2535CTG, MBR2545CTG

Switch-mode Power Rectifiers

The MBR2535CTG/45CTG series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- These are Pb-Free Devices*

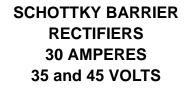
Mechanical Characteristics

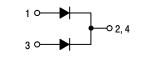
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

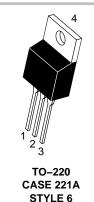


ON Semiconductor®

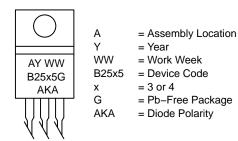
http://onsemi.com







MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
MBR2535CTG	TO-220 (Pb-Free)	50 Units/Rail
MBR2545CTG	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR2535CTG, MBR2545CTG

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR2535CTG MBR2545CTG	V _{RRM} V _{RWM} V _R	35 45	V	
Average Rectified Forward Current (Rated V_R , $T_C = 160^{\circ}C$) Per Device Per Diode	I _{F(AV)}	30 15	A	
Peak Repetitive Forward Current per Diode Leg (Rated V_R , Square Wave, 20 kHz, $T_C = 150^{\circ}C$)	I _{FRM}	30	А	
Non-Repetitive Peak Surge Current per Diode Leg (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	А	
Peak Repetitive Reverse Surge Current (2.0 µs, 1.0 kHz)	I _{RRM}	1.0	А	
Storage Temperature Range	T _{stg}	-65 to +175	°C	
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C	
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs	
ESD Ratings: Machine Model = C Human Body Model = 3B	ESD	> 400 > 8000	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit		
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 2)	${\sf R}_{ heta {\sf JC}} \ {\sf R}_{ heta {\sf JA}}$	1.5 50	°C/W		

2. When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS (Per Diode)

Symbol	Characteristic	Condition	Min	Тур	Мах	Unit
VF	Instantaneous Forward Voltage (Note 3)	$ I_{F} = 15 \text{ Amp, } T_{J} = 25^{\circ}\text{C} $ $ I_{F} = 15 \text{ Amp, } T_{J} = 125^{\circ}\text{C} $ $ I_{F} = 30 \text{ Amp, } T_{J} = 25^{\circ}\text{C} $ $ I_{F} = 30 \text{ Amp, } T_{J} = 125^{\circ}\text{C} $	- - -	_ 0.50 _ 0.65	0.62 0.57 0.82 0.72	V
۱ _R	Instantaneous Reverse Current (Note 3)	Rated dc Voltage, $T_J = 25^{\circ}C$ Rated dc Voltage, $T_J = 125^{\circ}C$	-	_ 9.0	0.2 25	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width = $300 \ \mu$ s, Duty Cycle $\le 2.0\%$.

MBR2535CTG, MBR2545CTG

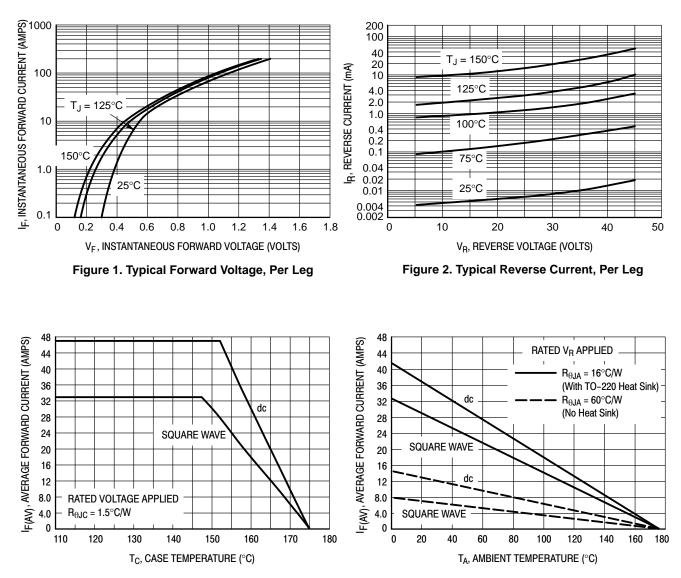


Figure 3. Current Derating, Per Device

Figure 4. Current Derating, Per Device

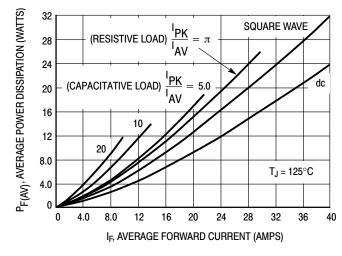


Figure 5. Forward Power Dissipation

S

onsemi

		TO-220 CASE 221A ISSUE AK						DATE	13 JAN 2022
SCALE 1:1			1. C 2. C 3. C	CONTR DIMEN LEAD	ROLLING DI ISION Z DEI D IRREGULA	MENSION FINES A ZO ARITIES AR	ONE WHERE AL E ALLOWED.		
			4. N	лах м	VIDTHFOR	F102 DEV	ICE = 1.35MM		
			Г		INC	HES	MILLIM	ETERS	
				ым 🛛	MIN.	MAX.	MIN.	MAX.	
	2 3			A	0.570	0.620	14.48	15.75	
				в	0.380	0.415	9.66	10.53	
н —	₩₩			с	0.160	0.190	4.07	4.83	
	7 \7	H I		D	0.025	0.038	0.64	0.96	
z_				F	0.142	0.161	3.60	4.09	
<u> </u>	I K			G	0.095	0.105	2.42	2.66	
				н	0.110	0.161	2.80	4.10	
	Щ Щ <u> </u>	Ü I		J	0.014	0.024	0.36	0.61	
	Г <mark>і</mark>			к	0.500	0.562	12.70	14.27	
V — + I I-	►- ``.			L	0.045	0.060	1.15	1.52	
G 	. <mark> </mark> ^{J−}			N	0.190	0.210	4.83	5.33	
· · · ·	- → D			Q	0.100	0.120	2.54	3.04	
	N 🖛			R	0.080	0.110	2.04	2.79	
				s	0.045	0.055	1.15	1.41	
				т	0.235	0.255	5.97	6.47	
				U	0.000	0.050	0.00	1.27	
				V	0.045		1.15		
				Z		0.080		2.04	
2. 3. 4. STYLE 5: PIN 1. 2.	BASE PIN 1. COLLECTOR 2. EMITTER 3. COLLECTOR 4. STYLE 6: GATE DRAIN 2.	EMITTER COLLECTOR EMITTER ANODE CATHODE	IN 1. CAT 2. ANO 3. GAT 4. ANO LE 7: IN 1. CAT 2. ANO	ode Te ode Thode ode		2. 3. 4. STYLE 8: PIN 1. 2.	MAIN TERMINAL MAIN TERMINAL GATE MAIN TERMINAL CATHODE ANODE	2	
4. STYLE 9: PIN 1.	DRAIN 4. STYLE 10 GATE PIN 1.	ANODE CATHODE GATE P SOURCE	3. CAT 4. ANO LE 11: IN 1. DR/ 2. SOU	ode Ain		4. STYLE 12: PIN 1.	EXTERNAL TRIP ANODE MAIN TERMINAL MAIN TERMINAL	. 1	
3.	EMITTER 3.	DRAIN SOURCE	3. GAT 4. SOL	ΤE		3.	GATE NOT CONNECTI		

 DOCUMENT NUMBER:
 98ASB42148B
 Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

 DESCRIPTION:
 TO-220
 PAGE 1 OF 1

 onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

MA4E2039 D1FH3-5063 MBR0530L-TP MBR10100CT-BP MBR1545CT MMBD301M3T5G RB160M-50TR RB551V-30 BAS16E6433HTMA1 BAT 54-02LRH E6327 NSR05F40QNXT5G NTE555 JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W SK310-T SK32A-LTP SK34B-TP SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP SK33B-TP SK38B-TP NRVBM120LT1G NTE505 NTSB30U100CT-1G SS15E-TP VS-6CWQ10FNHM3 ACDBA1100LR-HF ACDBA1200-HF ACDBA140-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF ACDBA340-HF ACDBA260LR-HF ACDBA1100-HF SK310B-TP MA4E2502L-1246 MA4E2502H-1246 NRVBM120ET1G NSR01L30MXT5G NTE573 NTE6081 SB560 PMAD1108-LF